

<b>Notice of References Cited</b>	Application/Control No. 10/564,486		Applicant(s)/Patent Under Reexamination SON, HYO-KUN	
	Examiner JESSE Y. MIYOSHI		Art Unit 2811	Page 1 of 1

#### U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-2003/0006418	01-2003	Emerson et al.	257/79
*	B	US-2002/0175341	11-2002	Biwa et al.	257/103
*	C	US-5,684,309	11-1997	McIntosh et al.	257/191
*	D	US-2004/0155248	08-2004	Fukuda et al.	257/079
*	E	US-6,614,059	09-2003	Tsujimura et al.	257/101
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

#### FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N	WO03005459	01-2003	International A	Yoshikatsu Fukuda	H01L21/285
	O					
	P					
	Q					
	R					
	S					
	T					

#### NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Kenji Uchida et al., "Photoluminescence Characteristics and Pit Formation of InGaN/GaN quantum-well structures grown on sapphire substrates by low-pressure metalorganic vapor phase epitaxy", Nov. 17 1998, Journal of Electronic Materials, vol. 28, No.3, 1999, pages 246-251.
	V	
	W	
	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
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